

## HF/VHF/UHF RF power N-channel MOSFETs

### Features

- Gold metallization
- Excellent thermal stability
- Common source push-pull configuration
- $P_{OUT} = 350\text{ W}$  min. with 21 dB gain @ 175 MHz
- In compliance with the 2002/95/EC European directive

### Description

The STAC2942F is a gold metallized N-channel MOS field-effect RF power transistor. It is intended for use in 50 V DC large signal applications up to 250 MHz.

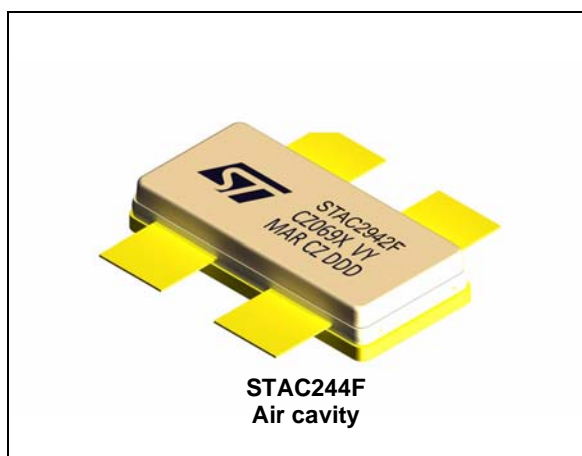


Figure 1. Pin connection

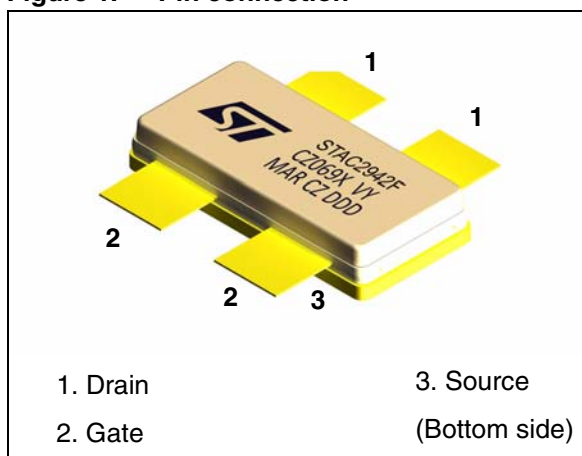


Table 1. Device summary

Order code	Marking	Package	Packaging
STAC2942FW	STAC2942F <sup>(1)</sup>	STAC244F	Plastic tray

1. For more details please refer to [Chapter 7: Marking, packing and shipping specifications](#).

# Contents

<b>1</b>	<b>Electrical data</b> .....	<b>3</b>
1.1	Maximum ratings .....	3
1.2	Thermal data .....	3
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Static .....	4
2.2	Dynamic .....	4
<b>3</b>	<b>Impedance</b> .....	<b>5</b>
<b>4</b>	<b>Typical performance</b> .....	<b>6</b>
<b>5</b>	<b>Test circuit</b> .....	<b>10</b>
<b>6</b>	<b>Package mechanical data</b> .....	<b>12</b>
<b>7</b>	<b>Marking, packing and shipping specifications</b> .....	<b>14</b>
<b>8</b>	<b>Revision history</b> .....	<b>15</b>

# 1 Electrical data

## 1.1 Maximum ratings

**Table 2. Absolute maximum ratings** ( $T_{CASE} = 25\text{ °C}$ )

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}^{(1)}$	Drain source voltage	130	V
$V_{DGR}^{(1)}$	Drain-gate voltage ( $R_{GS} = 1\text{ M}\Omega$ )	130	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current	40	A
$P_{DISS}$	Power dissipation	625	W
$T_J$	Max. operating junction temperature	200	$^{\circ}\text{C}$
$T_{STG}$	Storage temperature	-65 to +150	$^{\circ}\text{C}$

1.  $T_J = 150\text{ °C}$

## 1.2 Thermal data

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Junction - case thermal resistance	0.28	$^{\circ}\text{C/W}$

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$ )

### 2.1 Static

**Table 4. Static (per side)**

Symbol	Test conditions			Min.	Typ.	Max.	Unit
$V_{(BR)DSS}^{(1)}$	$V_{GS} = 0\text{ V}$	$I_{DS} = 100\text{ mA}$		130			V
$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 50\text{ V}$				100	$\mu\text{A}$
$I_{GSS}$	$V_{GS} = 20\text{ V}$	$V_{DS} = 0\text{ V}$				250	nA
$V_{GS(Q)}$	$V_{DS} = 10\text{ V}$	$I_D = 250\text{ mA}$		1.5	2.5	4.0	V
$V_{DS(ON)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$				3.0	V
$G_{FS}$	$V_{DS} = 10\text{ V}$	$I_D = 5\text{ A}$		5			S
$C_{ISS}$	$V_{GS} = 0\text{ V}$ $V_{DS} = 50\text{ V}$ $f = 1\text{ MHz}$				425		pF
$C_{OSS}$					202		pF
$C_{RSS}$					12		pF

1.  $T_J = 150\text{ °C}$

### 2.2 Dynamic

**Table 5. Dynamic**

Symbol	Test conditions	Min.	Typ.	Max.	Unit
$P_{OUT}$	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 2 \times 250\text{ mA}$ , $P_{IN} = 4\text{ W}$ , $f = 175\text{ MHz}$	350	450		W
$h_D$	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 2 \times 250\text{ mA}$ , $P_{IN} = 4\text{ W}$ , $f = 175\text{ MHz}$	60	75		%

### 3 Impedance

Figure 2. Current conventions

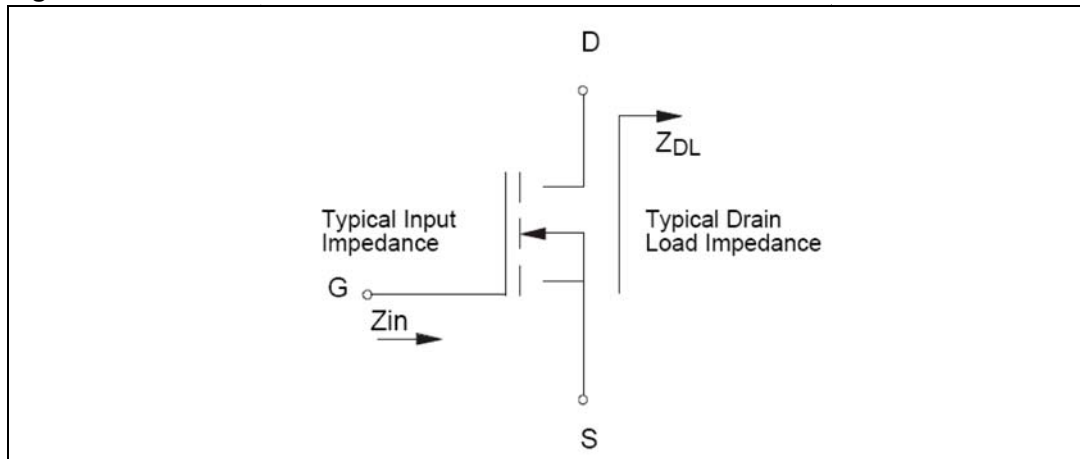


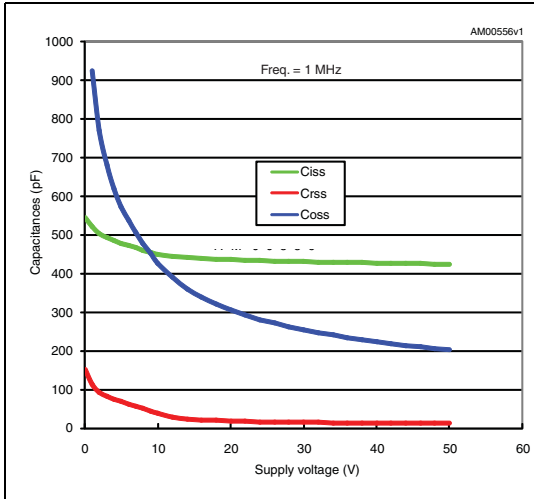
Table 6. Impedance data

Freq. (MHz)	$Z_{IN}$ ( $\Omega$ )	$Z_{DL}$ ( $\Omega$ )
175 MHz	$2.0 - j2.0$	$3.5 + j5.2$

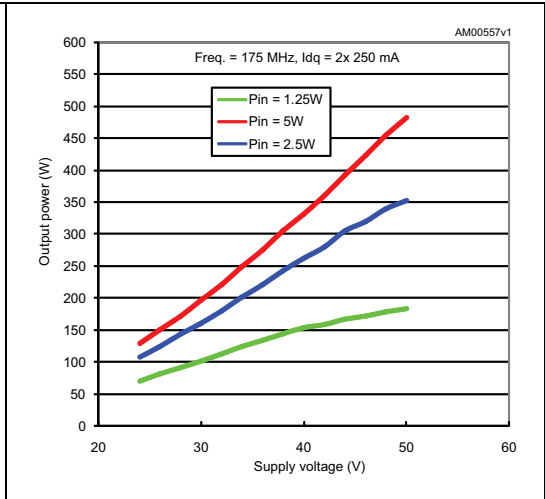
Note: Measured gate to gate and drain to drain, respectively.

# 4 Typical performance

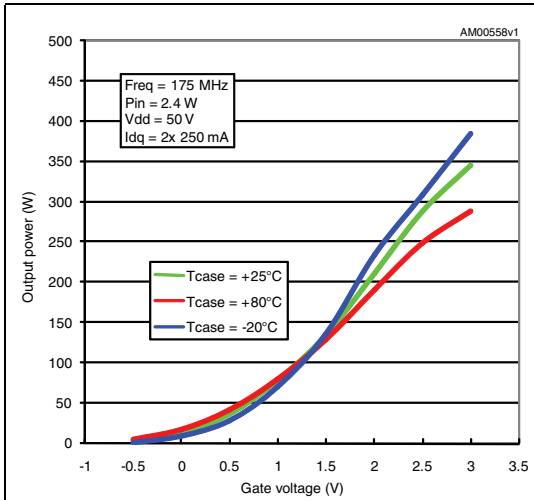
**Figure 3. Capacitances vs drain supply voltage**



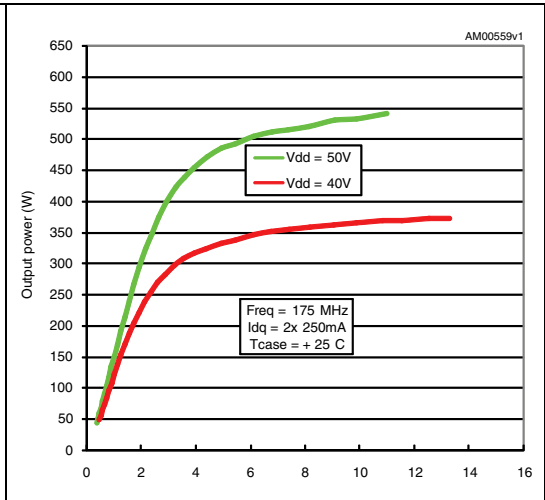
**Figure 4. Output power vs drain supply voltage**



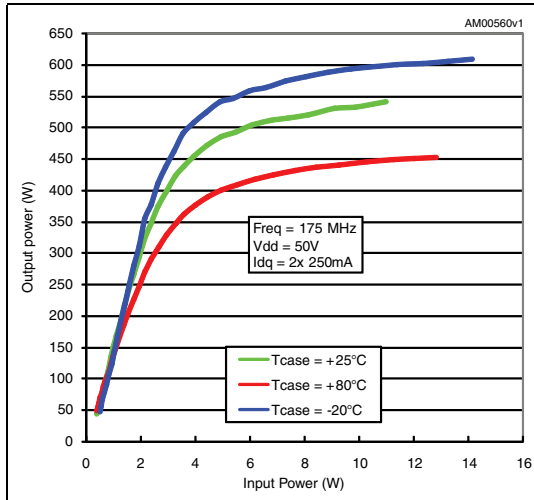
**Figure 5. Output power vs gate voltage**



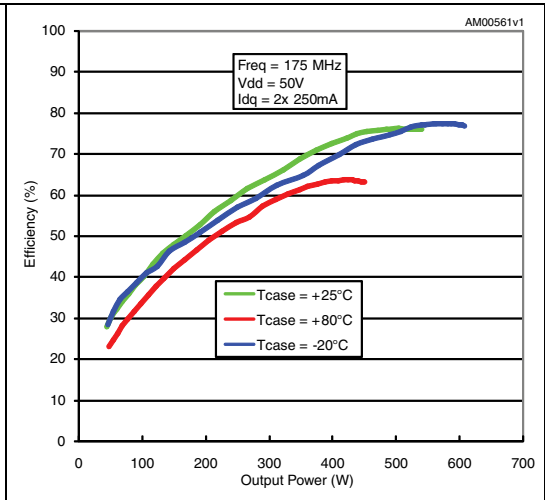
**Figure 6. Output power vs input power**



**Figure 7. Output power vs input power and case temperature**



**Figure 8. Efficiency vs output power and case temperature**



**Figure 9. Power gain vs output power and case temperature**

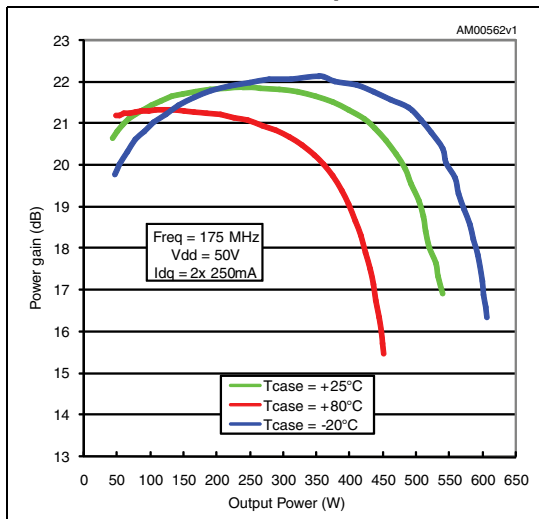


Figure 10. Maximum safe operating area

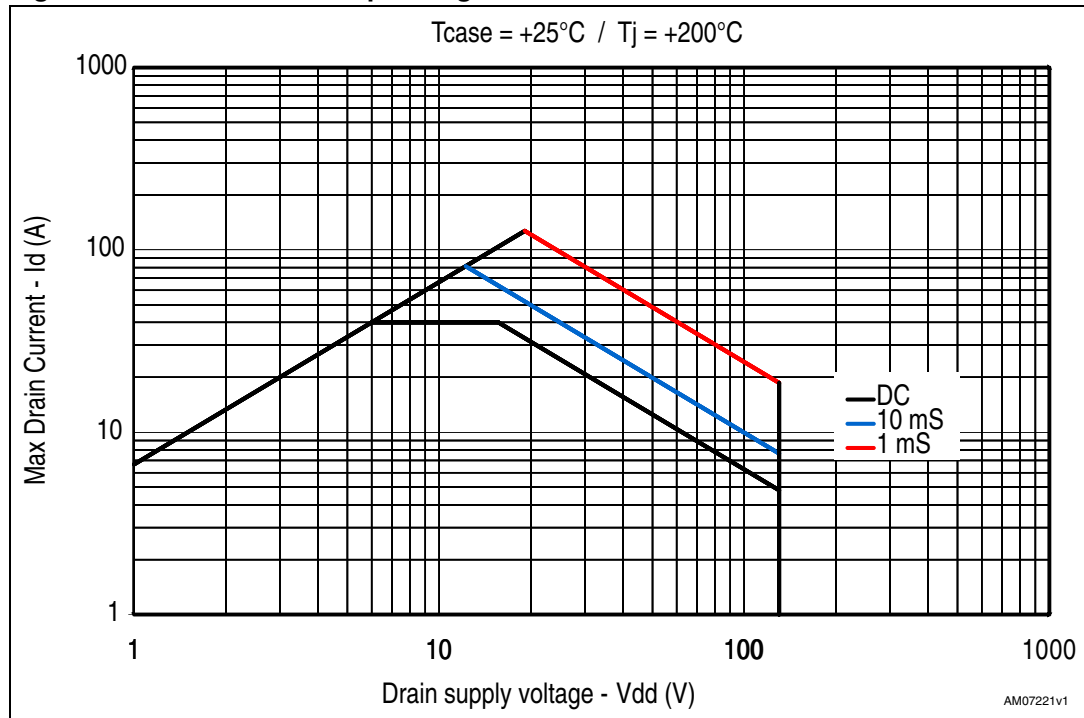


Figure 11. Transient thermal impedance

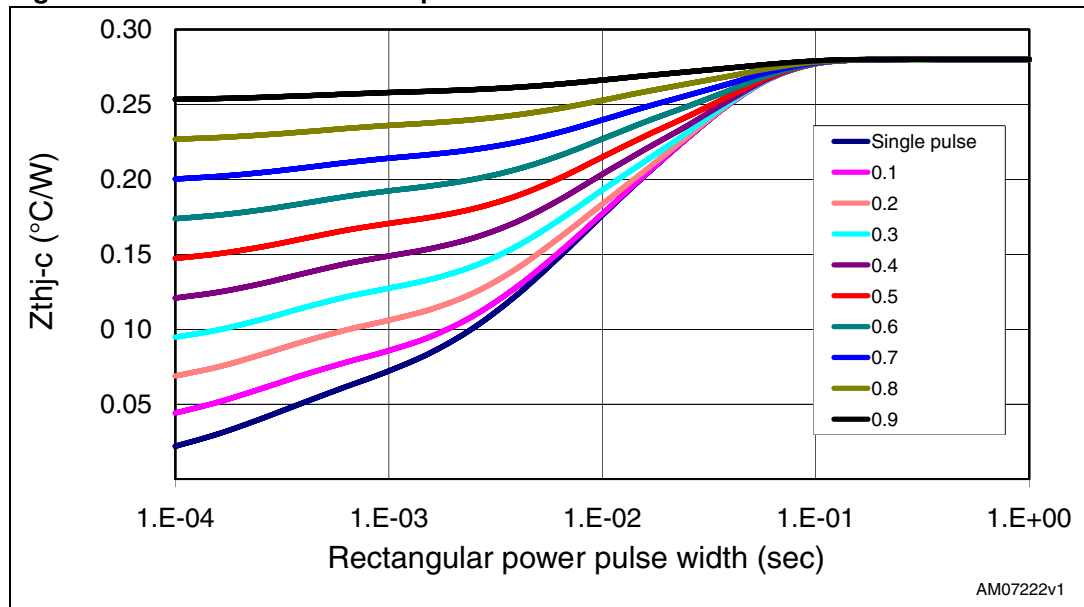
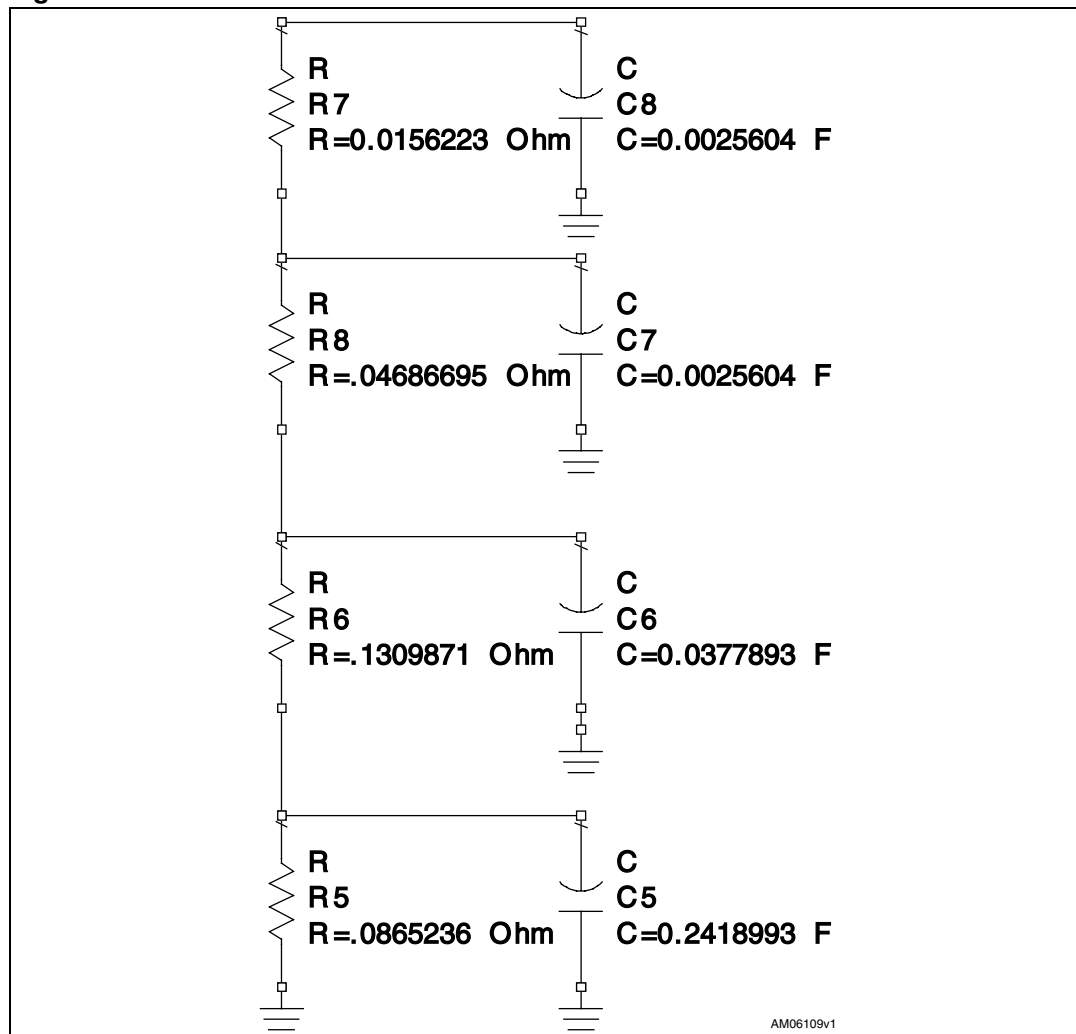




Figure 12. Transient thermal model



# 5 Test circuit

Figure 13. 175 MHz test circuit schematic (production test circuit)

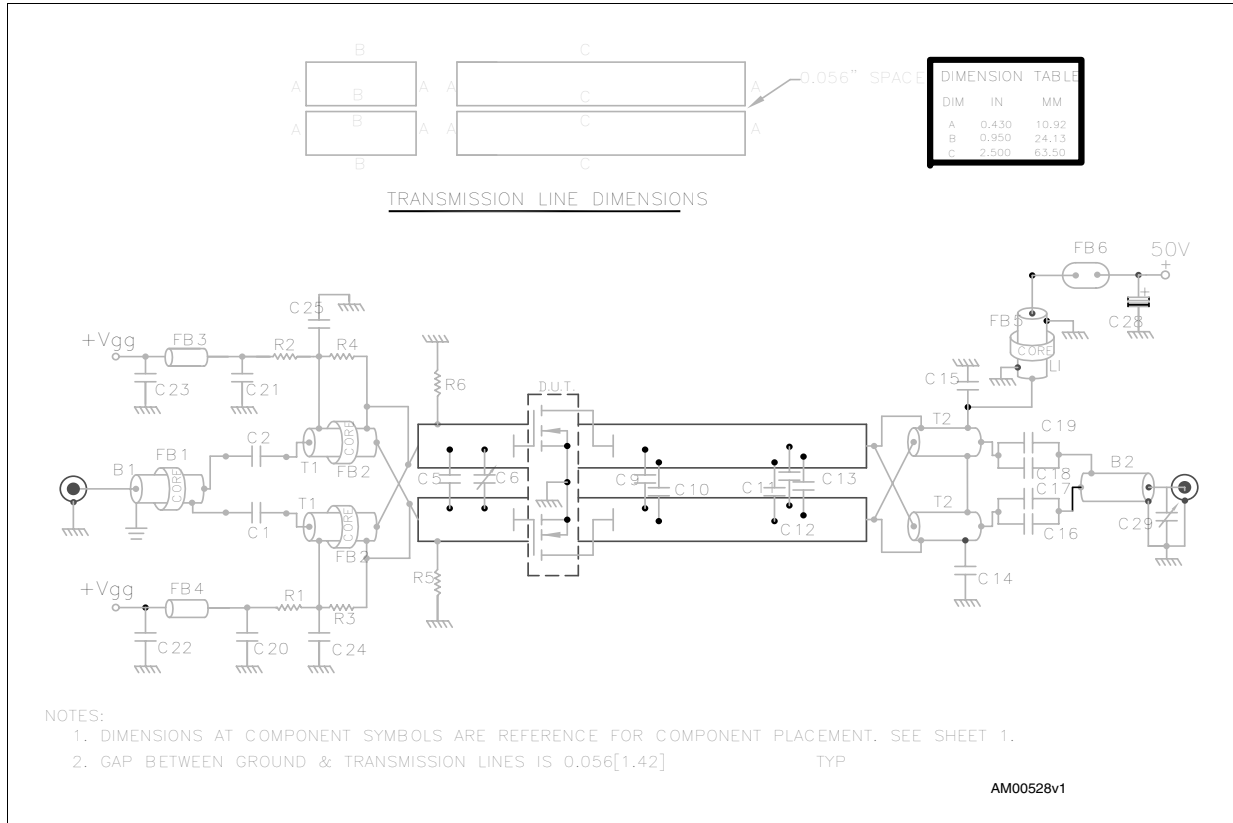


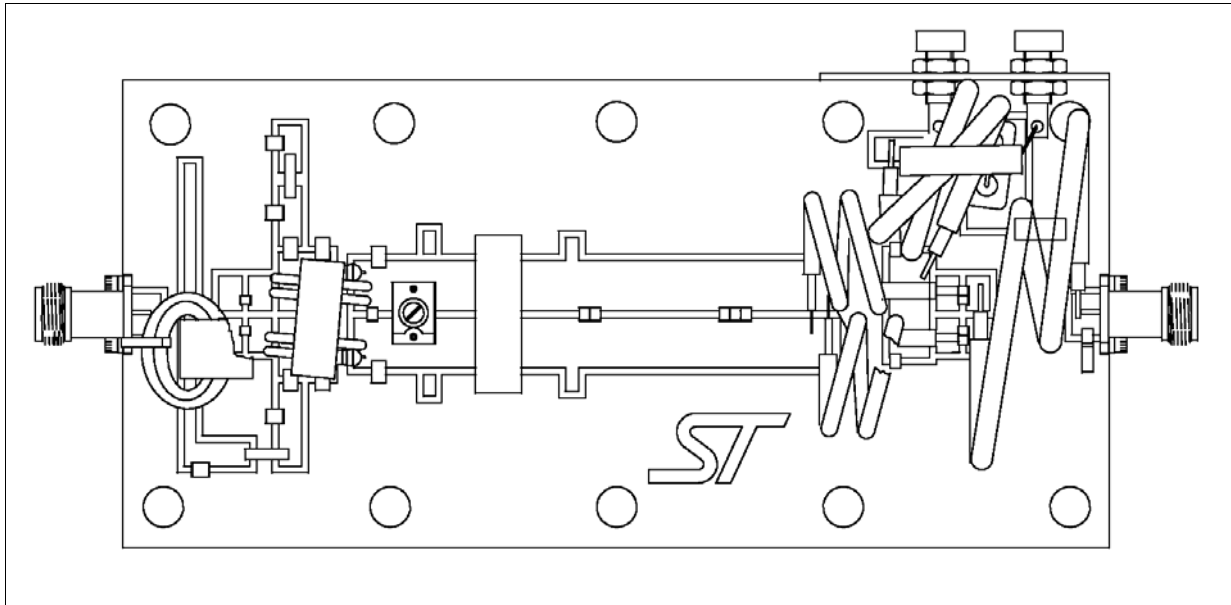
Table 7. 175 MHz test circuit component part list

Component	Description
C1, C2, C14, C15, C24, C25	1200 pF ATC 700B chip capacitor
C5	75 pF ATC 100B chip capacitor
C6	ST406 variable capacitor
C9, C10	47 pF ATC 100B chip capacitor
C11, C12, C13	43 pF ATC 100B chip capacitor
C16, C18	470 pF ATC 100B chip capacitor
C17, C19, C20, C21	10,000 pF ATC 200B chip capacitor
C22, C23	0.1 μF 200 V chip capacitor
C28	10 μF 100 V electrolytic capacitor
C29	0.8 - 8 pF variable capacitor
R1, R2, R5, R6	430 Ω 1/2 W chip resistor

Table 7. 175 MHz test circuit component part list (continued)

Component	Description
R3, R4	270 $\Omega$ 1/2 W axial lead resistor
B1	RG-316 50 $\Omega$ 11.8" thru ferrite toroid
B2	RG-142 50 $\Omega$ 11.8"
T1	4:1, RG-316 25 $\Omega$ , 5.9", 2 turns thru ferrite core
T2	1:4, 25 $\Omega$ semi-rigid cable, OD .141", 5.9"
L1	$\lambda/4$ inductor, RG-142 50 $\Omega$ 11.8", 3 turns thru ferrite toroid
FB1,FB5	Ferrite toroid
FB2, FB6	Multi-aperture core
FB3, FB4	Surface mount ferrite bead
PCB	Rogers ultralam 2000, Er 2.55, .060"

Figure 14. Circuit layout



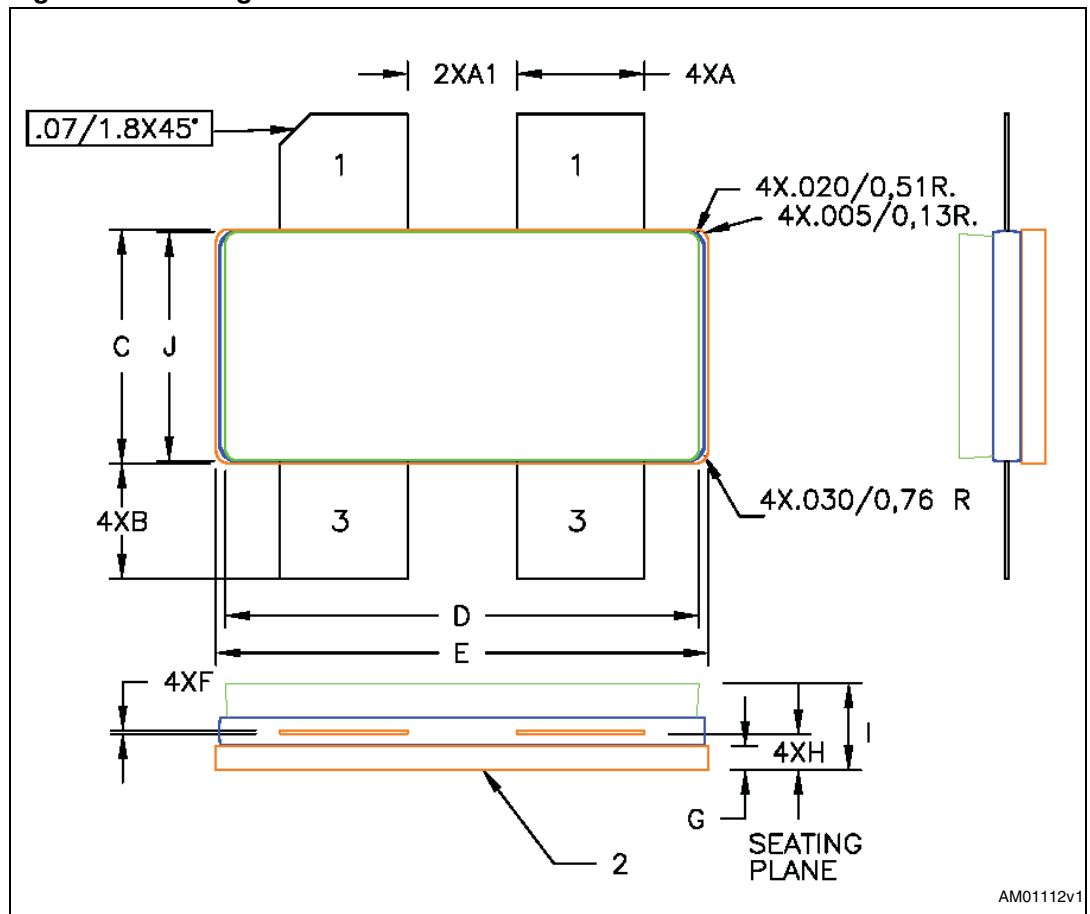
## 6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

**Table 8. STAC244F package dimensions**

Dim.	mm.		Inch	
	Min	Max	Min	Max
A	5.10	5.59	200	220
A1	4.32	4.83	170	190
B	4.32	5.33	170	210
C	9.65	9.91	380	390
D	19.61	20.02	772	788
E	20.45	20.70	805	815
F	0.08	1.15	.003	.006
G	0.89	1.14	.035	.045
H	1.45	1.70	.057	.067
I	3.18	4.32	.125	.170
J	9.27	9.53	.365	.375

Figure 15. Package dimensions

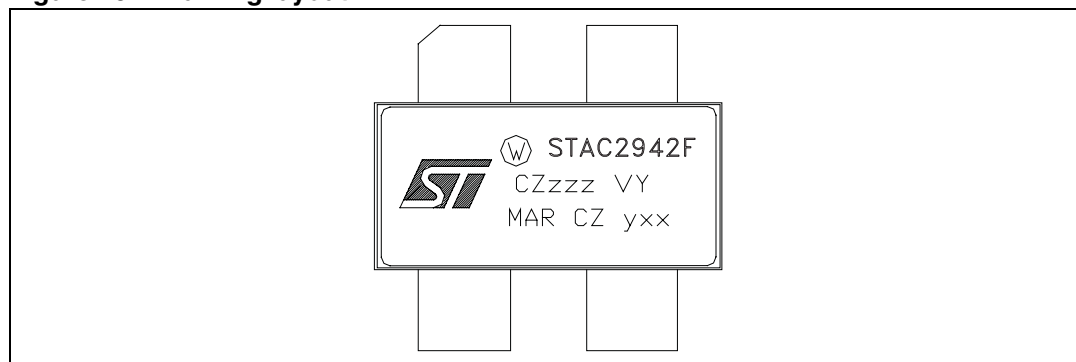


## 7 Marking, packing and shipping specifications

**Table 9. Packing and shipping specifications**

Order code	Packaging	Pcs per tray	Dry pack humidity	Lot code
STAC2942FW	Tube	20	< 10 %	Not mixed

**Figure 16. Marking layout**



**Table 10. Marking specifications**

Symbol	Description
W	Wafer process code
CZ	Assembly plant
xxx	Last 3 digit of diffusion lot
VY	Diffusion plant
MAR	Country of origin
CZ	Test and finishing plant
y	Assembly year
yy	Assembly week

## 8 Revision history

**Table 11. Document revision history**

Date	Revision	Changes
12-Feb-2010	1	First release.
16-Apr-2010	2	Added <i>Figure 10</i> , <i>Figure 11</i> and <i>Figure 12</i> .
25-Oct-2011	3	Added <i>Chapter 7: Marking, packing and shipping specifications</i> .

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